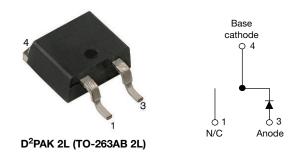
# VS-E5TH3012S2LHM3

Vishay Semiconductors

# Hyperfast Rectifier, 30 A FRED Pt<sup>®</sup> G5



### LINKS TO ADDITIONAL RESOURCES

1		
<u>3D M</u>	odels	

PRIMARY CHARACTERISTICS								
I <sub>F(AV)</sub>	30 A							
V <sub>R</sub>	1200 V							
V <sub>F</sub> at I <sub>F</sub> at 125 °C	1.7 V							
t <sub>rr</sub>	32 ns							
T <sub>J</sub> max.	175 °C							
Package	D <sup>2</sup> PAK 2L (TO-263AB 2L)							
Circuit configuration	Single							

### **FEATURES**

- Minimum creepage and clearance distances are 5.2 mm and 5.4 mm respectively
- Hyperfast and optimized Qrr
- Best in class forward voltage drop and switching 
   HALOGEN
   FREE
   losses trade off
- Optimized for high speed operation
- 175 °C maximum operating junction temperature
- Polyimide passivation
- Meets MSL level, per J-Std-020, LF maximum peak of 245 °C
- AEC-Q101 qualified meets JESD 201 class 2 whisker test
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

#### **DESCRIPTION / APPLICATIONS**

Featuring a unique combination of low conduction and switching losses, this rectifier is the right choice for high frequency converters, both soft switched / resonant.

Specifically designed to improve efficiency of PFC and output rectification stages of EV / HEV battery charging stations, booster stage of solar inverters and UPS applications, these devices are perfectly matched to operate with MOSFETs or high speed IGBTs.

#### **MECHANICAL DATA**

Case: D<sup>2</sup>PAK 2L (TO-263AB 2L)

Molding compound meets UL 94 V-0 flammability rating

**Terminals:** matte tin plated leads, solderable per J-STD-002

ABSOLUTE MAXIMUM RATINGS										
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS						
Repetitive peak reverse voltage	V <sub>RRM</sub>		1200	V						
Average rectified forward current	I <sub>F(AV)</sub>	T <sub>C</sub> = 96 °C, D = 0.50	30							
Non-repetitive peak surge current	I <sub>FSM</sub>	$T_{C}$ = 45 °C, $t_{p}$ = 10 ms, sine wave	240	A						
Repetitive peak forward current	I <sub>FRM</sub>	T <sub>C</sub> = 96 °C, D = 0.50, f = 20 kHz	60							
Operating junction and storage temperature	T <sub>J</sub> , T <sub>Stg</sub>		-55 to +175	°C						

<b>ELECTRICAL SPECIFICATIONS</b> ( $T_J = 25 \text{ °C}$ unless otherwise specified)									
PARAMETER	SYMBOL	TEST CONDITIONS	TEST CONDITIONS MIN. T						
Breakdown voltage, blocking voltage	$V_{BR}, V_{R}$	I <sub>R</sub> = 100 μA	1200	-	-				
Forward voltage	VF	I <sub>F</sub> = 30 A	-	1.9	2.5	V			
	۷F	I <sub>F</sub> = 30 A, T <sub>J</sub> = 125 °C	-	1.7	-				
Povereo lookago ourrent	1	$V_{R} = V_{R}$ rated	-	-	50				
Reverse leakage current	IR	$T_J = 125 \text{ °C}, V_R = V_R \text{ rated}$	-	-	500	μA			
Junction capacitance	CT	V <sub>R</sub> = 200 V	-	17	-	pF			
Series inductance	L <sub>S</sub>	Measured to lead 5 mm from package body	-	8	-	nH			

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COMPLIANT







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<b>DYNAMIC RECOVERY CHARACTERISTICS</b> ( $T_J = 25$ °C unless otherwise specified)										
PARAMETER	SYMBOL	TE	ST CONDITIONS	MIN.	TYP.	MAX.	UNITS			
Reverse recovery time		$I_F = 1.0 \text{ A}, \text{ d}I_F/\text{d}I_F$	t = 100 A/µs, V <sub>R</sub> = 30 V	-	32	-				
	t <sub>rr</sub>	$T_J = 25 \ ^\circ C$		-	113	-	ns			
		T <sub>J</sub> = 125 °C		-	175	-				
Peak recovery current	1	$T_J = 25 \ ^\circ C$	l <sub>F</sub> = 20 A dl <sub>F</sub> /dt = 600 A/µs	-	17	-	А			
	I <sub>RRM</sub>	T <sub>J</sub> = 125 °C	$V_{\rm B} = 400 \text{ V}$	-	24	-				
Reverse recovery charge	Q <sub>rr</sub>	T <sub>J</sub> = 25 °C		-	850	-	nC			
Reverse recovery charge		T <sub>J</sub> = 125 °C		-	2150	-				
Powerse recovery time	t <sub>rr</sub>	T <sub>J</sub> = 25 °C		-	85	-	ns			
Reverse recovery time		T <sub>J</sub> = 125 °C	]	-	132	-	115			
Pook receivery ourrent	1	T <sub>J</sub> = 25 °C	l <sub>F</sub> = 30 A dl <sub>F</sub> /dt = 1000 A/µs	-	30	-	А			
Peak recovery current	I <sub>RRM</sub>	T <sub>J</sub> = 125 °C	$V_{\rm B} = 800 \text{ V}$	-	43	-				
Powerse recovery charge	0	T <sub>J</sub> = 25 °C		-	1350	-	nC			
Reverse recovery charge	Q <sub>rr</sub>	T <sub>J</sub> = 125 °C		-	3215	-				

THERMAL - MECHANICAL SPECIFICATIONS										
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS				
Thermal resistance, junction-to-case	R <sub>thJC</sub>		-	-	1.1	°C/W				
Weight			-	2.0	-	g				
Mounting torque			6.0 (5.0)	-	12 (10)	kgf · cm (lbf · in)				
Maximum junction and storage temperature range	T <sub>J</sub> , T <sub>Stg</sub>		-55	-	175	°C				
Marking device		Case style D <sup>2</sup> PAK 2L (TO-263AB 2L)	E5TH3012SH							



### VS-E5TH3012S2LHM3

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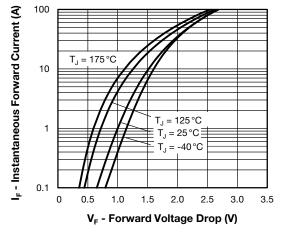


Fig. 1 - Typical Forward Voltage Drop Characteristics

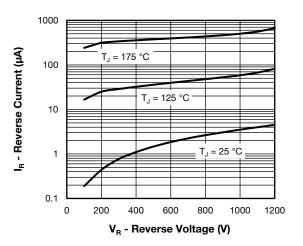


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

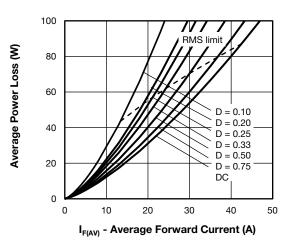


Fig. 5 - Forward Power Loss Characteristics

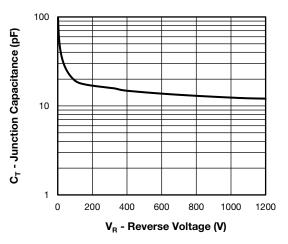


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

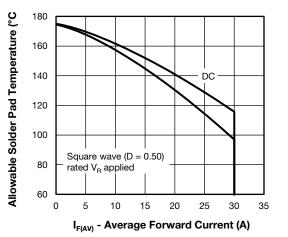


Fig. 4 - Maximum Allowable Case Temperature vs. Average Forward Current

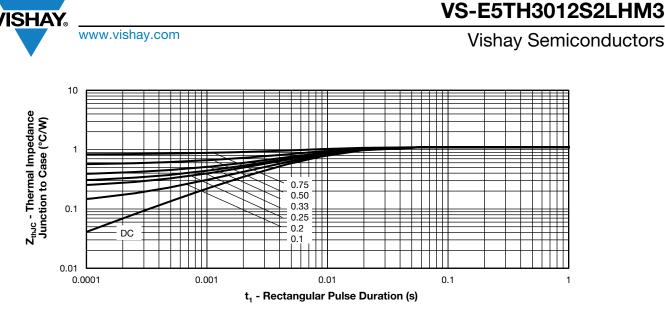


Fig. 6 - Thermal Impedance ZthJC Characteristics

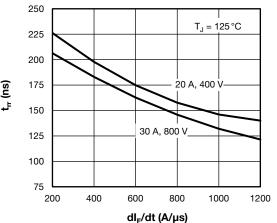
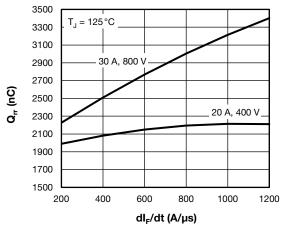
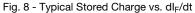


Fig. 7 - Typical Reverse Recovery Time vs. dI<sub>F</sub>/dt





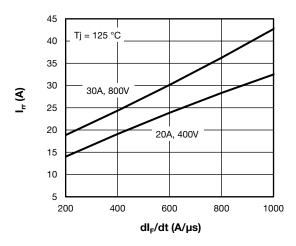


Fig. 9 - Typical Recovery Current vs. dI<sub>F</sub>/dt

 $\mathbf{t}_{\mathrm{rr}}$  (ns)





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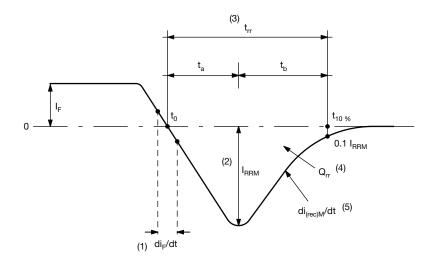


Fig. 10 - Reverse Recovery Waveform and Definitions

#### Notes

- $^{(1)}$  di<sub>F</sub>/dt rate of change of current through zero crossing
- <sup>(2)</sup> I<sub>RRM</sub> peak reverse recovery current
- <sup>(3)</sup>  $t_{rr}$  reverse recovery time measured from  $t_0$ , crossing point of negative going I<sub>F</sub>, to point  $t_{10\%}$ , 0.1 I<sub>RRM</sub>
- $^{(4)}~~\text{Q}_{rr}$  area under curve defined by  $t_0$  and  $t_{10~\%}$

$$Q_{rr} = \int_{t_0}^{t_{10\%}} I(t) dt$$

 $^{(5)}$  di<sub>(rec)</sub>M/dt - peak rate of change of current during t<sub>b</sub> portion of t<sub>rr</sub>





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### **ORDERING INFORMATION TABLE**

Device code	VS-	E	5	т	н	30	12	S2	L	н	М3	
	1	2	3	4	5	6	7	8	9	10	(11)	
	<ol> <li>Vishay Semiconductors product</li> <li>E single diade</li> </ol>											
		<ul> <li>E = single diode</li> <li>5 = FRED generation 5</li> </ul>										
	4 -	4 - Package: T = D <sup>2</sup> PAK (TO-262) package										
	5 -			ast recov	-							
	6 - 7 -			ing (30 = ing (12 =	-	/)						
		- S2	= true 2	pin D <sup>2</sup> F	PAK							
	<ul> <li>9 - None = tube (50 pieces)</li> <li>• L = tape and reel (left oriented, for D<sup>2</sup>PAK package) If needed different orientation/packaging, please contact factory</li> <li>10 - H = AEC-Q101 qualified</li> </ul>											
	<b>11</b> ·			ntal digit Jen-free,		complia	ant, and	termina	ation lea	d (Pb)-f	ree	

ORDERING INFORMATION (Example)								
PREFERRED P/N	BASE QUANTITY	PACKAGING DESCRIPTION						
VS-E5TH3012S2LHM3	800	13" diameter reel						

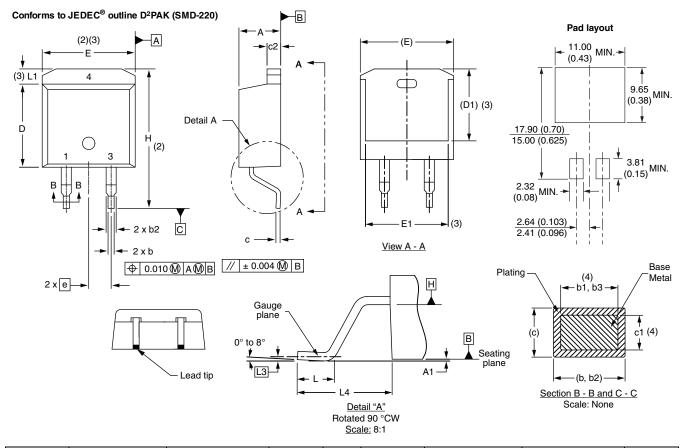
LINKS TO RELATED DOCUMENTS							
Dimensions	www.vishay.com/doc?96683						
Part marking information	www.vishay.com/doc?96693						
Packaging information	www.vishay.com/doc?95032						
SPICE Model	www.vishay.com/doc?96926						

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D<sup>2</sup>PAK 2L (TO-263AB 2L)

#### **DIMENSIONS** in millimeters and inches



SYMBOL	MILLIM	ETERS	INC	HES	NOTES			SYMBOL MILLIMETERS		INCHES		NOTES
STMBOL	MIN.	MAX.	MIN.	MAX.	NOTES	NOTES	STMBOL	MIN.	MAX.	MIN.	MAX.	NOTES
А	4.06	4.83	0.160	0.190			D1	6.86	8.00	0.270	0.315	3
A1	0.00	0.254	0.000	0.010			Е	9.65	10.67	0.380	0.420	2, 3
b	0.51	0.99	0.020	0.039			E1	7.90	8.80	0.311	0.346	3
b1	0.51	0.89	0.020	0.035	4		е	2.54	BSC	0.100	) BSC	
b2	1.14	1.78	0.045	0.070			Н	14.61	15.88	0.575	0.625	
b3	1.14	1.73	0.045	0.068	4		L	1.78	2.79	0.070	0.110	
с	0.38	0.74	0.015	0.029			L1	-	1.65	-	0.066	3
c1	0.38	0.58	0.015	0.023	4		L3	0.25 BSC		0.010 BSC		
c2	1.14	1.65	0.045	0.065			L4	4.78	5.28	0.188	0.208	
D	8.51	9.65	0.335	0.380	2							

#### Notes

<sup>(1)</sup> Dimensioning and tolerancing per ASME Y14.5 M-1994

(2) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body
 (3) Thermal and contain antional within dimension E 1.1, D1 and E1.

<sup>(3)</sup> Thermal pad contour optional within dimension E, L1, D1 and E1

<sup>(4)</sup> Dimension b1 and c1 apply to base metal only

<sup>(5)</sup> Datum A and B to be determined at datum plane H

<sup>(6)</sup> Controlling dimension: inch

(7) Outline conforms to JEDEC® outline TO-263AB

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